

NTST30100CTG, NTSB30100CT-1G, NTSJ30100CTG, NTSB30100CTG

Very Low Forward Voltage Trench-based Schottky Rectifier

Exceptionally Low $V_F = 0.455\text{ V}$ at $I_F = 5\text{ A}$

Features

- Fine Lithography Trench-based Schottky Technology for Very Low Forward Voltage and Low Leakage
- Fast Switching with Exceptional Temperature Stability
- Low Power Loss and Lower Operating Temperature
- Higher Efficiency for Achieving Regulatory Compliance
- Low Thermal Resistance
- High Surge Capability
- These are Pb-Free Devices

Typical Applications

- Switching Power Supplies including Notebook / Netbook Adapters, ATX and Flat Panel Display
- High Frequency and DC-DC Converters
- Freewheeling and OR-ing diodes
- Reverse Battery Protection
- Instrumentation

Mechanical Characteristics

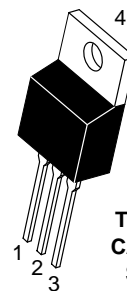
- Case: Epoxy, Molded
- Epoxy Meets Flammability Rating UL 94-0 @ 0.125 in
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Maximum for 10 sec



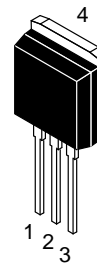
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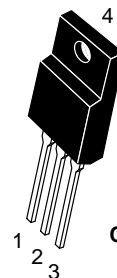
PIN CONNECTIONS



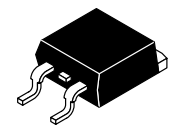
TO-220AB
CASE 221A
STYLE 6



I2PAK
CASE 418D
STYLE 3



TO-220FP
CASE 221AH



D2PAK
CASE 418B

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

NTST30100CTG, NTSB30100CT-1G, NTSJ30100CTG, NTSB30100CTG

MAXIMUM RATINGS

| Rating | Symbol | Value | Unit |
|--|--|-------------|------------------|
| Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage | V_{RRM} V_{RWM} V_R | 100 | V |
| Average Rectified Forward Current (Rated V_R , $T_C = 115^\circ\text{C}$) | $I_{F(AV)}$ Per device Per diode | 30 15 | A |
| Peak Repetitive Forward Current (Rated V_R , Square Wave, 20 kHz, $T_C = 110^\circ\text{C}$) | I_{FRM} Per device Per diode | 60 30 | A |
| Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz) | I_{FSM} | 160 | A |
| Operating Junction Temperature | T_J | -40 to +150 | $^\circ\text{C}$ |
| Storage Temperature | T_{stg} | -40 to +150 | $^\circ\text{C}$ |
| Voltage Rate of Change (Rated V_R) | dv/dt | 10,000 | V/ μs |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

| Rating | Symbol | NTST30100CTG, NTSB30100CT-1G | NTSB30100CTG | NTSJ30100CTG | Unit |
|---|------------------------------------|---------------------------------|--------------|--------------|--|
| Maximum Thermal Resistance per Diode Junction-to-Case Junction-to-Ambient | $R_{\theta JC}$ $R_{\theta JA}$ | 2.5 70 | 1.14 46.6 | 4.09 105 | $^\circ\text{C/W}$ $^\circ\text{C/W}$ |

ELECTRICAL CHARACTERISTICS (Per Leg unless otherwise noted)

| Rating | Symbol | Typ | Max | Unit |
|---|--------|--|--------------------------------------|--|
| Maximum Instantaneous Forward Voltage (Note 1) ($I_F = 5\text{ A}$, $T_J = 25^\circ\text{C}$) ($I_F = 7.5\text{ A}$, $T_J = 25^\circ\text{C}$) ($I_F = 15\text{ A}$, $T_J = 25^\circ\text{C}$) ($I_F = 5\text{ A}$, $T_J = 125^\circ\text{C}$) ($I_F = 7.5\text{ A}$, $T_J = 125^\circ\text{C}$) ($I_F = 15\text{ A}$, $T_J = 125^\circ\text{C}$) | V_F | 0.516 0.576 0.734 0.455 0.522 0.627 | - - 0.85 - - 0.68 | V |
| Maximum Instantaneous Reverse Current (Note 1) ($V_R = 70\text{ V}$, $T_J = 25^\circ\text{C}$) ($V_R = 70\text{ V}$, $T_J = 125^\circ\text{C}$) (Rated dc Voltage, $T_J = 25^\circ\text{C}$) (Rated dc Voltage, $T_J = 125^\circ\text{C}$) | I_R | 7.2 8.0 65 20 | 500 35 | μA mA μA mA |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: Pulse Width = 300 μs , Duty Cycle $\leq 2.0\%$

TYPICAL CHARACTERISTICS

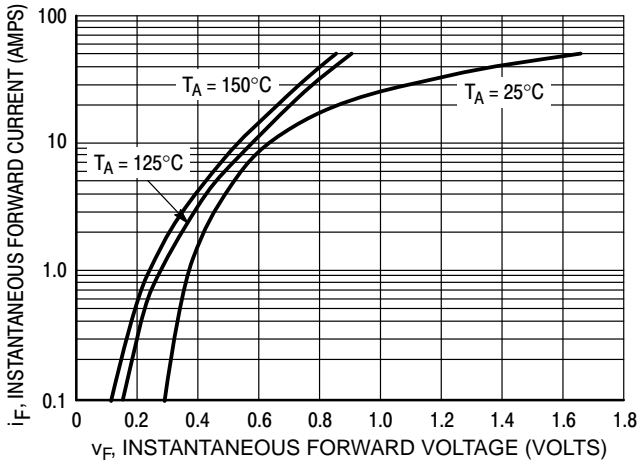


Figure 1. Typical Forward Voltage

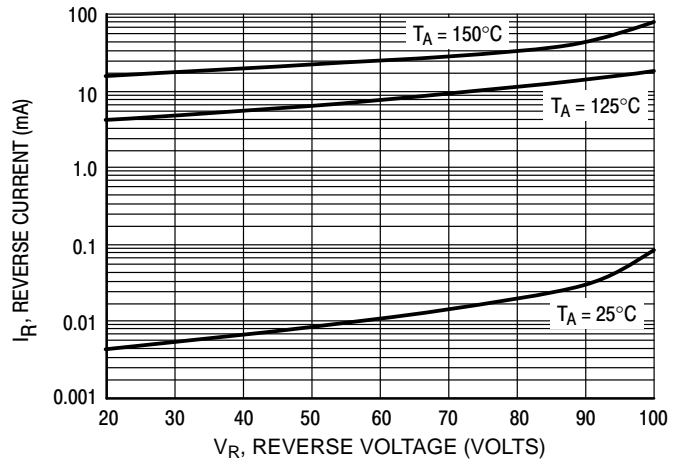


Figure 2. Typical Reverse Current

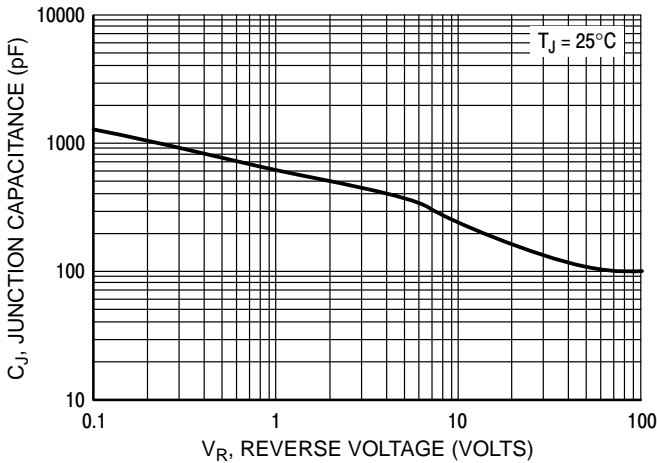


Figure 3. Typical Junction Capacitance

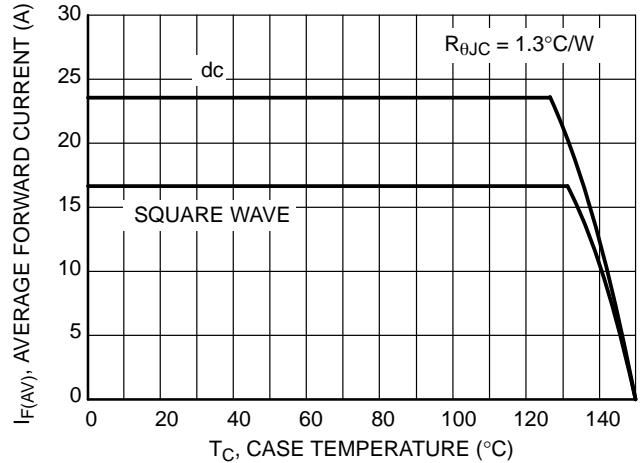


Figure 4. Current Derating per Leg

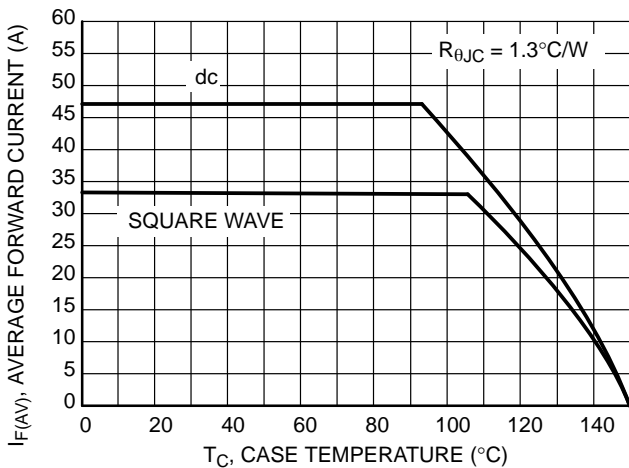


Figure 5. Current Derating

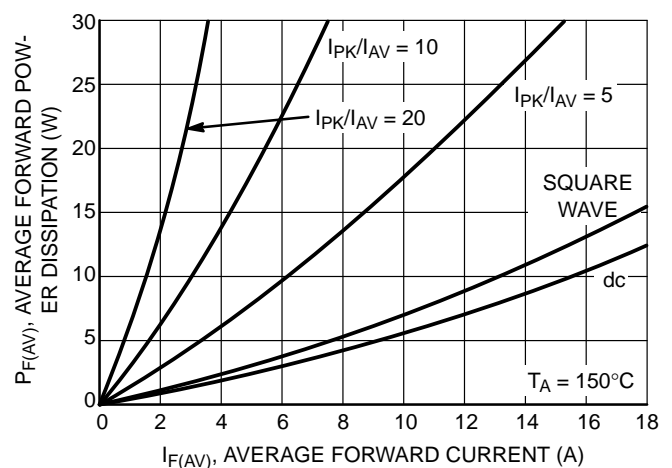


Figure 6. Forward Power Dissipation

TYPICAL CHARACTERISTICS

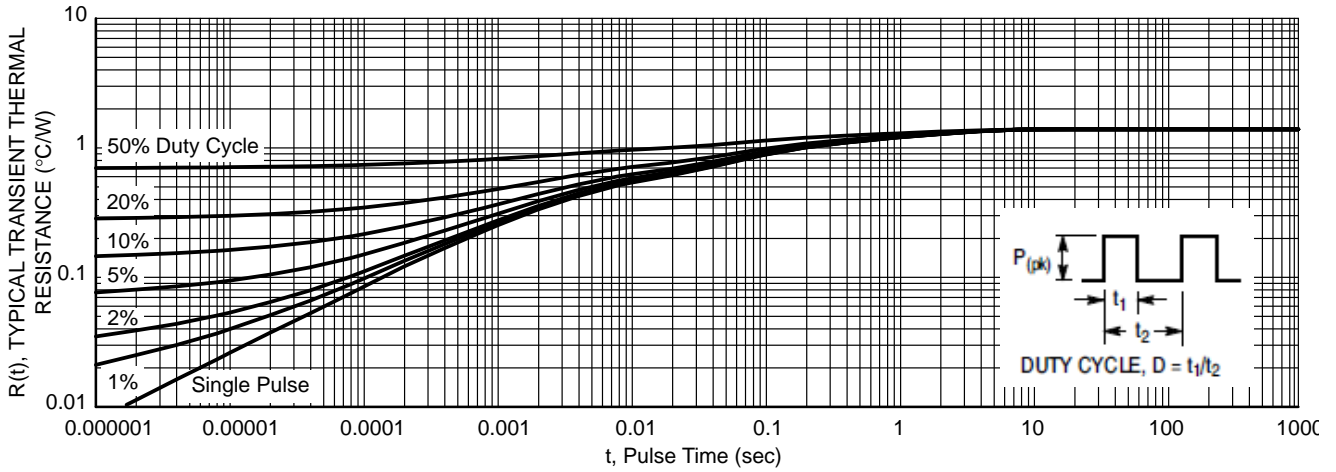


Figure 7. Typical Transient Thermal Response, Junction-to-Case for NTST30100CT and NTSB30100CT-1G

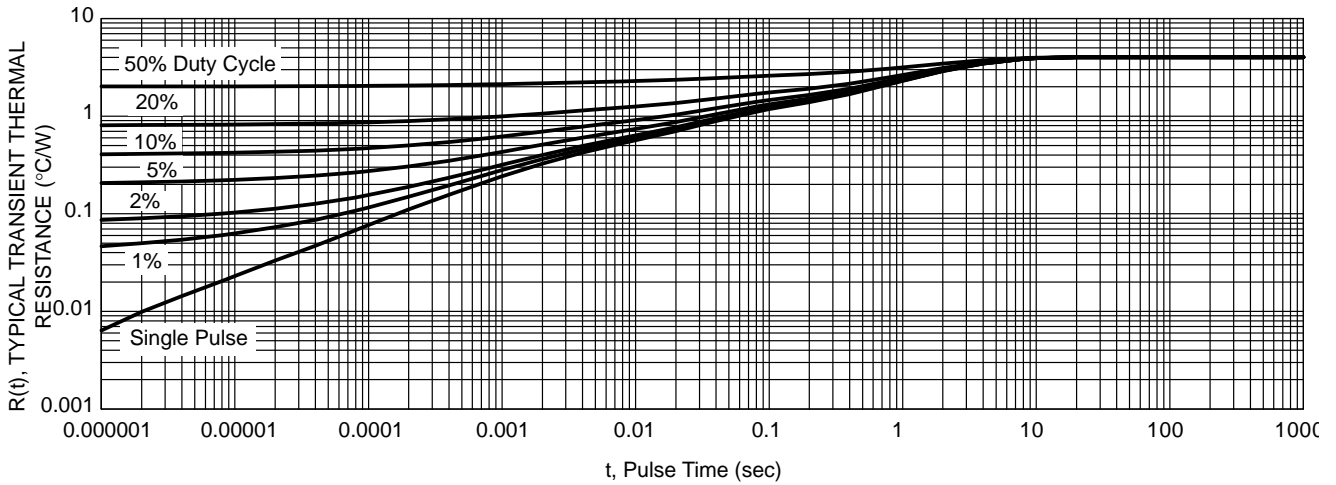


Figure 8. Typical Transient Thermal Response, Junction-to-Case for NTSJ30100CTG

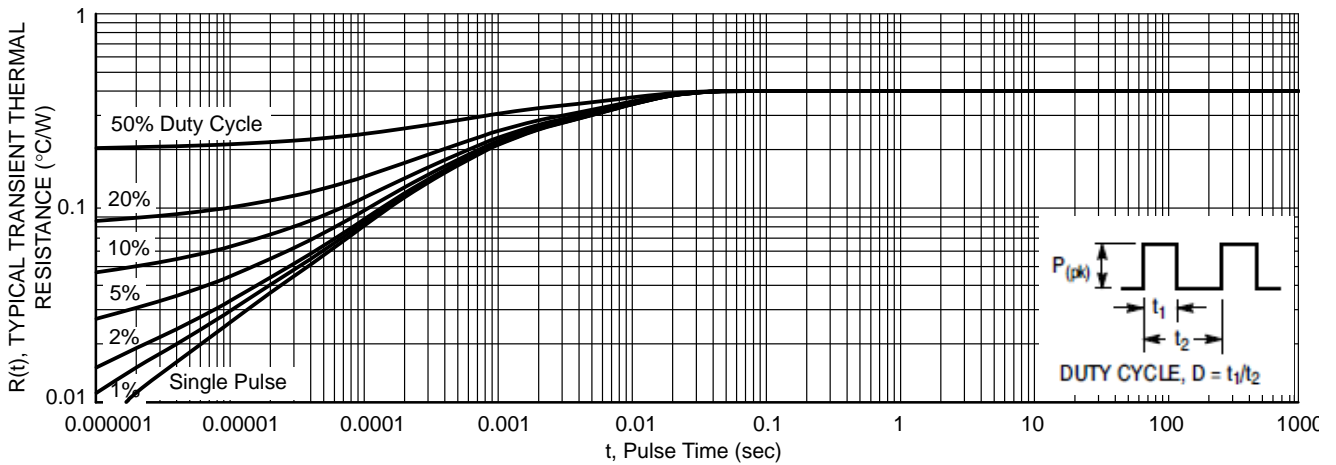


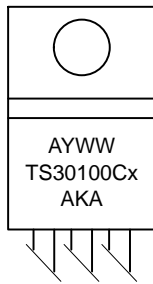
Figure 9. Typical Transient Thermal Response, Junction-to-Case for NTSB30100CTG

NTST30100CTG, NTSB30100CT-1G, NTSJ30100CTG, NTSB30100CTG

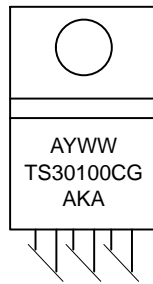
ORDERING INFORMATION

| Device | Package | Shipping |
|----------------|---------------------------------|-------------------|
| NTST30100CTG | TO-220AB (Pb-Free) | 50 Units / Rail |
| NTSB30100CT-1G | I ² PAK (Pb-Free) | 50 Units / Rail |
| NTSJ30100CTG | TO-220FP (Halide-Free) | 50 Units / Rail |
| NTSB30100CTG | D ² PAK (Pb-Free) | 50 Units / Rail |
| NTSB30100CTT4G | D ² PAK (Pb-Free) | 800 / Tape & Reel |

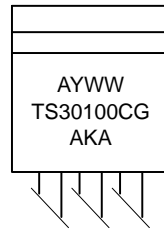
MARKING DIAGRAMS



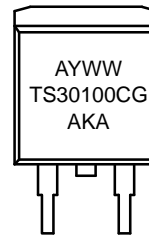
TO-220AB



TO-220FP



I²PAK



D²PAK

- A = Assembly Location
- Y = Year
- WW = Work Week
- AKA = Polarity Designator
- x = G or H
- G = Pb-Free Package
- H = Halide-Free Package

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

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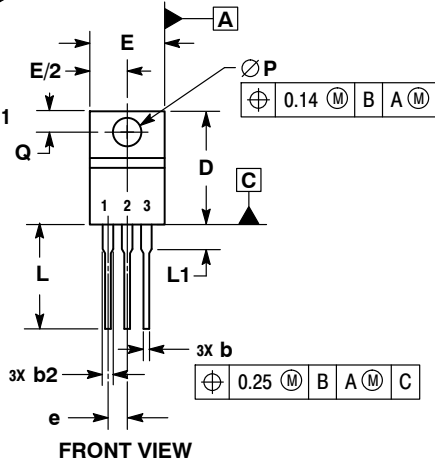


TO-220 FULLPACK, 3-LEAD CASE 221AH ISSUE F

DATE 30 SEP 2014



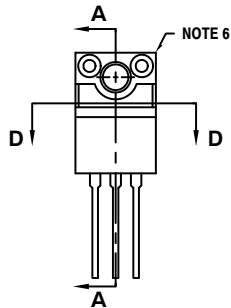
SCALE 1:1



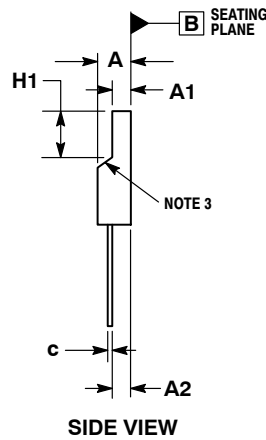
FRONT VIEW



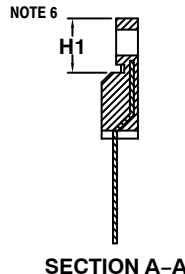
SECTION D-D



ALTERNATE CONSTRUCTION



SIDE VIEW



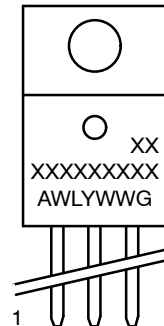
SECTION A-A

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. CONTOUR UNCONTROLLED IN THIS AREA.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH AND GATE PROTRUSIONS. MOLD FLASH AND GATE PROTRUSIONS NOT TO EXCEED 0.13 PER SIDE. THESE DIMENSIONS ARE TO BE MEASURED AT OUTERMOST EXTREME OF THE PLASTIC BODY.
5. DIMENSION b2 DOES NOT INCLUDE DAMBAR PROTRUSION. LEAD WIDTH INCLUDING PROTRUSION SHALL NOT EXCEED 2.00.
6. CONTOURS AND FEATURES OF THE MOLDED PACKAGE BODY MAY VARY WITHIN THE ENVELOPE DEFINED BY DIMENSIONS A1 AND H1 FOR MANUFACTURING PURPOSES.

| DIM | MILLIMETERS | |
|-----|-------------|-------|
| | MIN | MAX |
| A | 4.30 | 4.70 |
| A1 | 2.50 | 2.90 |
| A2 | 2.50 | 2.90 |
| b | 0.54 | 0.84 |
| b2 | 1.10 | 1.40 |
| c | 0.49 | 0.79 |
| D | 14.70 | 15.30 |
| E | 9.70 | 10.30 |
| e | 2.54 BSC | |
| H1 | 6.60 | 7.10 |
| L | 12.50 | 14.73 |
| L1 | --- | 2.80 |
| P | 3.00 | 3.40 |
| Q | 2.80 | 3.20 |

GENERIC MARKING DIAGRAM*



- A = Assembly Location
- WL = Wafer Lot
- Y = Year
- WW = Work Week
- G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

STYLE 1:

1. MAIN TERMINAL 1
2. MAIN TERMINAL 2
3. GATE

STYLE 2:

1. CATHODE
2. ANODE
3. GATE

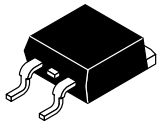
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MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

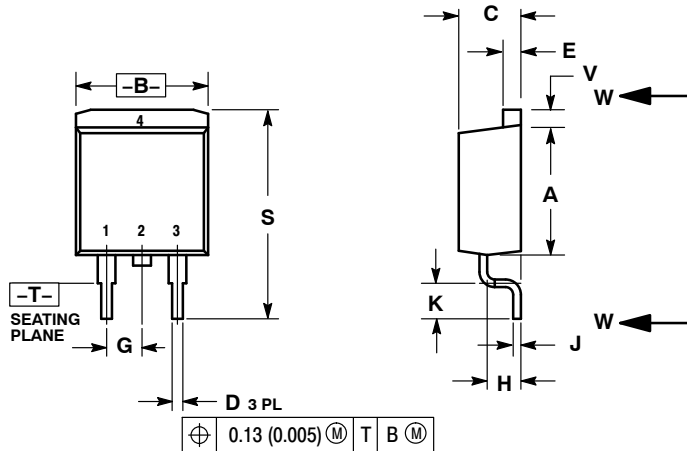
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D²PAK 3
CASE 418B-04
ISSUE L

DATE 17 FEB 2015

SCALE 1:1

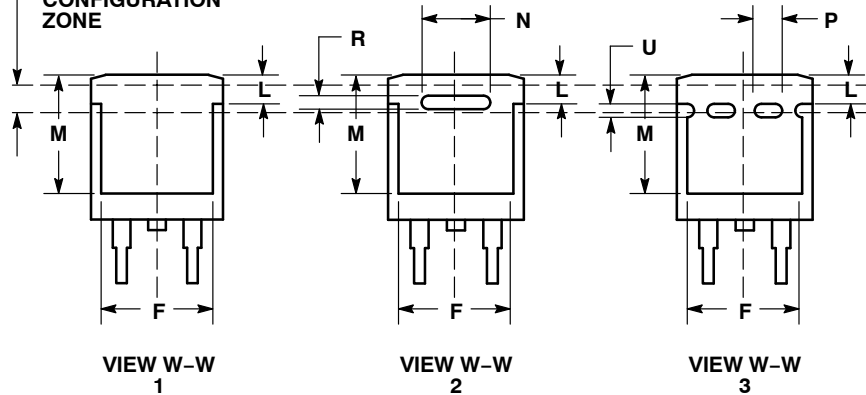


NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: INCH.
- 418B-01 THRU 418B-03 OBSOLETE, NEW STANDARD 418B-04.

| DIM | INCHES | | MILLIMETERS | |
|-----|--------|-------|-------------|-------|
| | MIN | MAX | MIN | MAX |
| A | 0.340 | 0.380 | 8.64 | 9.65 |
| B | 0.380 | 0.405 | 9.65 | 10.29 |
| C | 0.160 | 0.190 | 4.06 | 4.83 |
| D | 0.020 | 0.035 | 0.51 | 0.89 |
| E | 0.045 | 0.055 | 1.14 | 1.40 |
| F | 0.310 | 0.350 | 7.87 | 8.89 |
| G | 0.100 | BSC | 2.54 | BSC |
| H | 0.080 | 0.110 | 2.03 | 2.79 |
| J | 0.018 | 0.025 | 0.46 | 0.64 |
| K | 0.090 | 0.110 | 2.29 | 2.79 |
| L | 0.052 | 0.072 | 1.32 | 1.83 |
| M | 0.280 | 0.320 | 7.11 | 8.13 |
| N | 0.197 | REF | 5.00 | REF |
| P | 0.079 | REF | 2.00 | REF |
| R | 0.039 | REF | 0.99 | REF |
| S | 0.575 | 0.625 | 14.60 | 15.88 |
| V | 0.045 | 0.055 | 1.14 | 1.40 |

VARIABLE CONFIGURATION ZONE



- | | | | | | |
|--|---|---|--|---|--|
| STYLE 1: PIN 1. BASE 2. COLLECTOR 3. EMITTER 4. COLLECTOR | STYLE 2: PIN 1. GATE 2. DRAIN 3. SOURCE 4. DRAIN | STYLE 3: PIN 1. ANODE 2. CATHODE 3. ANODE 4. CATHODE | STYLE 4: PIN 1. GATE 2. COLLECTOR 3. EMITTER 4. COLLECTOR | STYLE 5: PIN 1. CATHODE 2. ANODE 3. CATHODE 4. ANODE | STYLE 6: PIN 1. NO CONNECT 2. CATHODE 3. ANODE 4. CATHODE |
|--|---|---|--|---|--|

MARKING INFORMATION AND FOOTPRINT ON PAGE 2

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D²PAK 3
CASE 418B-04
ISSUE L

DATE 17 FEB 2015

**GENERIC
MARKING DIAGRAM***



- xx = Specific Device Code
- A = Assembly Location
- WL = Wafer Lot
- Y = Year
- WW = Work Week
- G = Pb-Free Package
- AKA = Polarity Indicator

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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